Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.50 \text{ V}$ at $I_F = 5 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- This is a Pb-Free Package

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

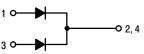
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec



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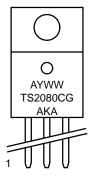
PIN CONNECTIONS





TO-220FP CASE 221AH

MARKING DIAGRAMS



A = Assembly Location

Y = Year

WW = Work Week
AKA = Polarity Designator

G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	80	V
Average Rectified Forward Current (Rated V_R , $T_C = 130^{\circ}C$)	Per device Per diode	I _{F(AV)}	20 10	А
Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 125°C)	Per device Per diode	I _{FRM}	40 20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	150	А
Operating Junction Temperature		TJ	-40 to +150	°C
Storage Temperature		T _{stg}	-40 to +150	°C
Voltage Rate of Change (Rated V _R)		dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (insertion mounted to 1 oz FR4 Board)	Junction-to-Case	$R_{\theta JC}$	4.0	°C/W
	Junction-to-Ambient	$R_{\theta JA}$	105	°C/W

Junction-to-Case, using large Heatsink attached to device.
 Junction-to-Ambient, using with no Heatsink.

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 3) $ (I_F = 5 \text{ A}, T_J = 25^{\circ}\text{C}) $ $ (I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C}) $	VF	0.55 0.65	- 0.83	V
(I _F = 5 A, T _J = 125°C) (I _F = 10 A, T _J = 125°C)		0.50 0.58	_ 0.68	
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C)	I _R	- 6	600 20	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$

ORDERING INFORMATION

Device	Package	Shipping
NTSJ2080CTG	TO-220FP (Halide-Free)	50 Units / Rail

TYPICAL CHARACTERISITICS

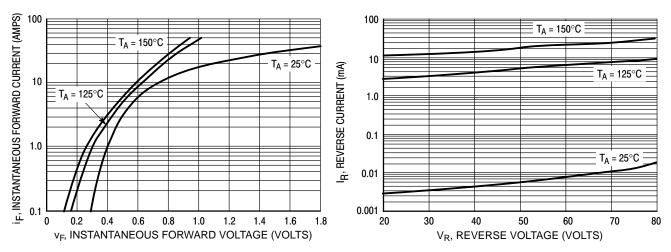


Figure 1. Typical Forward Voltage

Figure 2. Typical Reverse Current

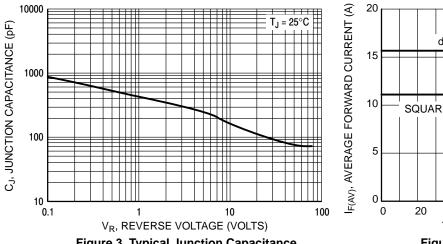


Figure 3. Typical Junction Capacitance

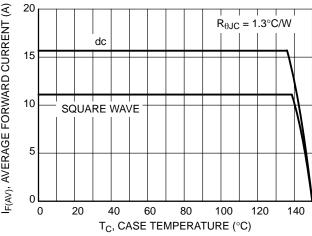
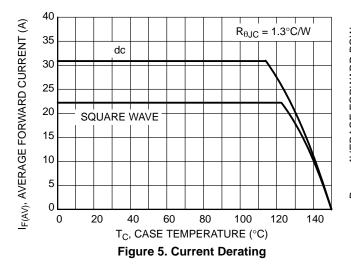


Figure 4. Current Derating per Leg



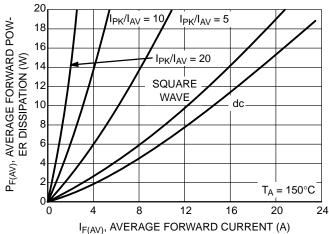


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISITICS

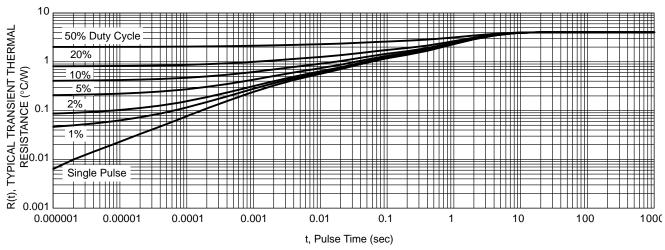
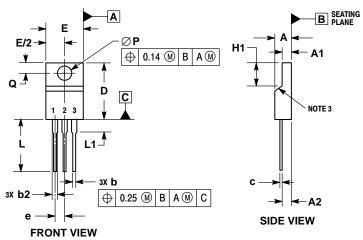


Figure 7. Typical Transient Thermal Response, Junction-to-Case

PACKAGE DIMENSIONS

TO-220 FULLPACK, 3-LEAD

CASE 221AH ISSUE F

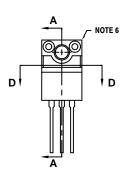


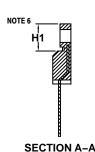
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR UNCONTROLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE. PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY.
- DIMENSION 62 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.
- CONTOURS AND FEATURES OF THE MOLDED PACKAGE BODY MAY VARY WITHIN THE ENVELOP DEFINED BY DIMENSIONS A1 AND H1 FOR MANUFACTURING PURPOSES.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.30	4.70	
A1	2.50	2.90	
A2	2.50	2.90	
b	0.54	0.84	
b2	1.10	1.40	
С	0.49	0.79	
D	14.70	15.30	
E	9.70	10.30	
е	2.54 BSC		
H1	6.60	7.10	
L	12.50	14.73	
L1		2.80	
P	3.00	3.40	
Q	2.80	3.20	







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